

Saulius Marcinkevicius

List of Publications by Year in descending order

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Version: 2024-02-01

60
papers

1,153
citations

304743

22
h-index

414414

32
g-index

61
all docs

61
docs citations

61
times ranked

1122
citing authors

#	ARTICLE	IF	CITATIONS
1	Transient electromagnetically induced transparency in self-assembled quantum dots. Applied Physics Letters, 2008, 92, .	3.3	93
2	Iron as a source of efficient Shockley-Read-Hall recombination in GaN. Applied Physics Letters, 2016, 109, .	3.3	64
3	Localization potentials in AlGaIn epitaxial films studied by scanning near-field optical spectroscopy. Journal of Applied Physics, 2011, 109, 113516.	2.5	54
4	Photoexcited carrier recombination in wide m -plane InGaIn/GaN quantum wells. Applied Physics Letters, 2013, 103, .	3.3	46
5	Ultrafast carrier trapping in Be-doped low-temperature-grown GaAs. Applied Physics Letters, 1999, 75, 3336-3338.	3.3	42
6	Electron and Hole Capture Cross-Sections of Fe Acceptors in GaN:Fe Epitaxially Grown on Sapphire. Journal of Electronic Materials, 2007, 36, 1621-1624.	2.2	40
7	Carrier localization in m -plane InGaIn/GaN quantum wells probed by scanning near field optical spectroscopy. Applied Physics Letters, 2010, 97, 151106.	3.3	40
8	Aging of AlGaIn quantum well light emitting diode studied by scanning near-field optical spectroscopy. Applied Physics Letters, 2009, 95, .	3.3	36
9	Optical properties of extended and localized states in m -plane InGaIn quantum wells. Applied Physics Letters, 2013, 102, .	3.3	36
10	Time-resolved luminescence studies of proton-implanted GaN. Applied Physics Letters, 2009, 95, .	3.3	35
11	Highly polarized photoluminescence and its dynamics in semipolar $(202\bar{1}\bar{1})$ InGaIn/GaN quantum well. Applied Physics Letters, 2014, 104, .	3.3	33
12	Optical absorption edge broadening in thick InGaIn layers: Random alloy atomic disorder and growth mode induced fluctuations. Applied Physics Letters, 2018, 112, .	3.3	31
13	Interwell carrier transport in InGaAsP multiple quantum well laser structures. Applied Physics Letters, 1996, 69, 3695-3697.	3.3	30
14	Optical studies of degradation of AlGaIn quantum well based deep ultraviolet light emitting diodes. Journal of Applied Physics, 2010, 108, .	2.5	30
15	Evidence of trap-assisted Auger recombination in low radiative efficiency MBE-grown III-nitride LEDs. Journal of Applied Physics, 2019, 126, .	2.5	30
16	Optically detected carrier transport in III/V semiconductor QW structures: experiments, model calculations and applications in fast $1.55\ \mu\text{m}$ laser devices. Applied Physics B: Lasers and Optics, 1998, 66, 1-17.	2.2	29
17	Dynamics of polarized photoluminescence in m -plane InGaIn/GaN quantum wells. Journal of Applied Physics, 2010, 108, 023101.	2.5	27
18	High spatial uniformity of photoluminescence spectra in semipolar $(202\bar{1}\bar{1})$ plane InGaIn/GaN quantum wells. Journal of Applied Physics, 2015, 117, 023111.	2.5	27

#	ARTICLE	IF	CITATIONS
19	Near-field investigation of spatial variations of (202\AA^{-1}) InGaN quantum well emission spectra. Applied Physics Letters, 2013, 103, 131116.	3.3	26
20	Photoexcited carrier trapping and recombination at Fe centers in GaN. Journal of Applied Physics, 2016, 119, .	2.5	26
21	Screening dynamics of intrinsic electric field in AlGaIn quantum wells. Applied Physics Letters, 2008, 92, .	3.3	25
22	Impact of carrier localization on radiative recombination times in semipolar (202\AA^{-1}) plane InGaIn/GaN quantum wells. Applied Physics Letters, 2015, 107, .	3.3	22
23	Intervalley energy of GaN conduction band measured by femtosecond pump-probe spectroscopy. Physical Review B, 2016, 94, .	3.2	21
24	Interwell carrier transport in InGaIn/(In)GaIn multiple quantum wells. Applied Physics Letters, 2019, 114, .	3.3	21
25	Ultrafast dynamics of hole self-localization in $\text{InGaIn}/\text{Ga}_2\text{O}_3$. Applied Physics Letters, 2020, 116, .	3.3	21
26	High spectral uniformity of AlGaIn with a high Al content evidenced by scanning near-field photoluminescence spectroscopy. Applied Physics Letters, 2014, 105, .	3.3	20
27	Electrochemical etching of AlGaIn for the realization of thin-film devices. Applied Physics Letters, 2019, 115, 182103.	3.3	20
28	Carrier redistribution between different potential sites in semipolar (202\AA^{-1}) InGaIn quantum wells studied by near-field photoluminescence. Applied Physics Letters, 2014, 105, .	3.3	17
29	Scanning near-field microscopy of carrier lifetimes in m-plane InGaIn quantum wells. Applied Physics Letters, 2017, 110, .	3.3	16
30	Polarization-Resolved Near-Field Spectroscopy of Localized States in m -Plane InGaIn Quantum Wells. Physical Review Applied, 2017, 7, .	3.8	16
31	Direct Measurement of Nanoscale Lateral Carrier Diffusion: Toward Scanning Diffusion Microscopy. ACS Photonics, 2018, 5, 528-534.	6.6	16
32	Carrier lifetimes in AlGaIn quantum wells: electric field and excitonic effects. Journal Physics D: Applied Physics, 2008, 41, 155116.	2.8	14
33	Dynamics of carrier recombination and localization in AlGaIn quantum wells studied by time-resolved transmission spectroscopy. Applied Physics Letters, 2009, 95, 091910.	3.3	14
34	Non-thermal photoexcited electron distributions in non-stoichiometric GaAs. Semiconductor Science and Technology, 1997, 12, 396-400.	2.0	13
35	Influence of well width fluctuations on recombination properties in semipolar InGaIn quantum wells studied by time- and spatially-resolved near-field photoluminescence. Optical Materials Express, 2017, 7, 3116.	3.0	11
36	Vertical carrier transport in InGaAsP multiple-quantum-well laser structures: effect of p-doping. IEEE Journal of Selected Topics in Quantum Electronics, 1997, 3, 315-319.	2.9	10

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37	Optical properties and carrier dynamics in m-plane InGaN quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 690-693.	0.8	10
38	High internal quantum efficiency of long wavelength InGaN quantum wells. Applied Physics Letters, 2021, 119, .	3.3	10
39	Impact of surface morphology on the properties of light emission in InGaN epilayers. Applied Physics Express, 2018, 11, 051004.	2.4	9
40	The Effect of Barrier Composition on the Vertical Carrier Transport and Lasing Properties of 1.55- μm Multiple Quantum-Well Structures. IEEE Journal of Quantum Electronics, 2006, 42, 713-724.	1.9	8
41	Transient photorefectance of AlInN/GaN heterostructures. AIP Advances, 2012, 2, .	1.3	8
42	Variations of light emission and carrier dynamics around V-defects in InGaN quantum wells. Journal of Applied Physics, 2020, 128, 225703.	2.5	8
43	Photon Walk in Transparent Wood: Scattering and Absorption in Hierarchically Structured Materials. Advanced Optical Materials, 2022, 10, .	7.3	8
44	Hole distribution in InGaAsP 1.3- μm multiple-quantum-well laser structures with different hole confinement energies. IEEE Journal of Quantum Electronics, 1999, 35, 603-607.	1.9	7
45	Carrier Dynamics in InGaAs/GaAs Quantum Dots. Physica Status Solidi (B): Basic Research, 1997, 204, 290-292.	1.5	6
46	Properties of near-field photoluminescence in green emitting single and multiple semipolar (202 \AA^{-1}) plane InGaN/GaN quantum wells. Optical Materials Express, 2016, 6, 39.	3.0	6
47	Low-temperature carrier transport across InGaN multiple quantum wells: Evidence of ballistic hole transport. Physical Review B, 2020, 101, .	3.2	6
48	Scanning near-field optical spectroscopy of AlGaIn epitaxial layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1617-1620.	0.8	4
49	Optimization of barrier height in InGaN quantum wells for rapid interwell carrier transport and low nonradiative recombination. Applied Physics Express, 2020, 13, 122005.	2.4	4
50	Electron-phonon scattering in In^{2+} -Ga ₂ O ₃ studied by ultrafast transmission spectroscopy. Applied Physics Letters, 2021, 118, .	3.3	3
51	Optimization of InGaN quantum well interfaces for fast interwell carrier transport and low nonradiative recombination. , 2022, , .		2
52	Carrier dynamics and localization in AlInN/GaN heterostructures. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 853-856.	0.8	1
53	Top-Down Fabrication of High Quality Gallium Indium Phosphide Nanopillar/disk Array Structures. , 2019, , .		1
54	Carrier trapping due to Fe ³⁺ /Fe ²⁺ in InP. , 0, , .		0

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55	Interwell Carrier Distribution in InAlGaAs Quantum Well Laser Structures. Physica Status Solidi (B): Basic Research, 1997, 204, 577-580.	1.5	0
56	Subpicosecond carrier capture into intermixed InGaAs/GaAs quantum dots. , 0, , .		0
57	Nanophotonics: A tutorial. , 2012, , .		0
58	Spatial variations of optical properties of semipolar InGaN quantum wells. Proceedings of SPIE, 2015, , .	0.8	0
59	Scanning near-field optical microscopy of AlGaIn epitaxial layers. Proceedings of SPIE, 2016, , .	0.8	0
60	Multimode Scanning Near-Field Photoluminescence Spectroscopy of InGaN Quantum Wells. , 2018, , .		0